Transm ission spectra of Fe/M g0 (001) double-barrier tunnel junctions at nite bias

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In this contribution, we calculate in a self-consistent way the ballistic transm ission as a function of energy of one Fe/M gO (001) single-barrier and one double-barrier tunnel junction, relating them to their electronic structure. The transm ission spectra of each kind of junction is calculated at di erent applied bias voltages. We focus on the impact that bias has on the resonant tunneling m ediated by surface and quantum well states. The calculations are done in the coherent regime, using a combination of density functional theory and non-equilibrium G reen's functions, as im plemented in the ab initio code SM EAGOL.

We conclude that, for both kinds of junction, the transm ission functions depend on the applied bias voltage. In the single-barrier junction, transport mediated by resonant Fe m inority surface states is rapidly destroyed by bias. In the double-barrier junction, the appearance of resonant tunneling through majority quantum well states is strongly a ected by bias.

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I. IN TRODUCTION

M agnetic tunnel junctions (M T Js), consisting of a sem iconducting barrier sandw iched by two ferrom agnetic electrodes, are prototype nanoscale systems exhibiting spin-dependent electronic transport, and are now adays being intensively investigated due to their potential applicability in spintronic devices based on the tunneling m agnetoresistance e ect (TMR). Besides their practical im portance, M T Js are interesting heterostructures on their own since they allow us to test our electronic transport theories and m odels, and to understand the com plex relationship that the electronic, m agnetic, and interface structures have with novel spin-dependent transport phenom ena (see R efs. [1] and references therein).

O ne of the main challenges in this eld is to obtain larger TM R and $V_{1=2}$ values (the bias voltage value at which the TM R drops to half its value at in nitesimal bias), both aspects being critical for device applications [2, 3]. As rst suggested by Zhang et al [4] a decade ago, a possible route to accomplish these higher values is to use double-barrier M T Js (D BM T Js), in which a m etallic slab (m agnetic or not) is inserted in between the sem iconducting spacer. In these junctions, whose m agnetic and transport properties have been m easured only very recently [3, 5, 6, 7], and whose transport properties have been calculated mainly using free electron m odels or non-selfconsistently [8], the in-between m etallic slab plays a dual role. First, it introduces quantum well states which can, in principle, couple to the evanescent states in the spacer, thus producing conductance resonances in some spin channel and therefore enhancing the TM R [4, 6, 7, 8, 9]. Second, if it is magnetic, it introduces a spin-dependent potential energy pro le which may act as an additional spin lter, again enhancing the TM R [7, 10, 11].

In particular, Fe/M g0 (001) single-and double-barrier junctions are ideal system s to study and good candidates for applications, since they show very large TMR values and can be now adays grown epitaxially with controlled interfaces. For example, T. Nozaki et al [5, 6] have recently m easured the TMR of Fe/M gO (001) SBM T Js and identically grown DBM TJs as a function of the applied voltage and found that the DBM TJs show larger TM R and $V_{1=2}$ values. Similar ndings have been reported in double-barrier junctions of other materials [3]. A lthough a complete understanding of these features (particularly the larger $V_{1=2}$ values) is still lacking, we have recently shown by ab initio calculations on Fe/MgO DBMTJs [11] that the spin-lter e ect, introduced by the magnetic in-between Fe layers, is one of their origins. On the other hand, A. Jovan et al [7] have recently m easured extrem ely large TMR values (an order of magnitude larger than those of identically grown M T Js) and conductance oscillations in Fe/M gO DBM TJs, originated from resonant tunneling processes m ediated by spin-split quantum well states. Sim ilar conductance oscillations in Fe/M gO DBM TJs have been reported by Nozaki et al as well [6]. From the theoretical side, Y. W ang et al [9] have shown, from rst principles, that the sm all conductance oscillations observed [6] in Fe/M gO DBM TJs originate from the majority $_1$ -symmetry QWS at the point. which e ciently couples to a decaying state in the M gO spacer. From these examples it is clear that DBM TJs

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are prom ising candidates for spintronic applications, and consequently that further theoretical and experimental studies of these heterostructures are necessary to fully understand the role of QW Ss and, especially, of the bias voltage on their spin-dependent transport properties.

W ith this aim in m ind, here we calculate the coherent transm ission spectra of idealFe/M gO (001) SBM T Js and DBM TJs at di erent values of the applied bias voltages. The focus is put on the impact that this bias voltage has on the transm ission resonancesm ediated by quantum well states in DBM TJs and by surface states in SBM TJs [1, 12]. To this end, we employ the self-consistent ab initio SMEAGOL code [13, 14], which is based on a combination of the SESTA package [15] and the nonequilibrium Green's function formalism [16]. By extending the work of Y.W ang et al [9] that considered only the point, we take into account a large num ber of wave vectors inside the surface Brillouin Zone. Furtherm ore, the transport calculations are perform ed self-consistently, taking full account of the non-equilibrium electronic population inside the junction induced by a nite applied bias voltage to the Fe electrodes. We have already presented the calculated characteristic curves of Fe/M gO (001) SBM TJs and DBM TJs and discussed the di erent transport mechanisms elsewhere [11], reaching qualitative agreem ent with available experim ental results. Here, we would like to focus on the impact that a bias voltage has on these mechanisms, emphasizing the di erences between the transmission functions in the singleand double-barrier cases.

II. CALCULATION DETAILS

O ur SBM T Js consist of 2 m onolayers (M Ls) of M gO (001), representing 4 A, sandwiched by two sem i-in nite bcc Fe (001) electrodes, while our D BM T Js are multilayers of the type (M gO)₂/Fe_m / (M gO)₂ (001) sandwiched by the same electrodes. The number of in-between Fe m onolayers is set equal to m = 2 M Ls, representing 2.87 A. In both cases, the junctions are assumed to be periodic in the x-y plane, being z the transport direction. In this work, we restrict to the parallelm agnetic con guration of the junctions (hereafter denoted P), in which the m agnetization vector in every m agnetic region is parallel to each other.

In order to account for the charge transfer and to correctly reproduce the band o set between Fe and M gO, we include in the cell for self-consistent calculations four Fe M Ls belonging to the electrodes at both sides of the junction. This in enough to correctly account for charge screening inside the ferrom agnet. Sim ilar to previous calculations [9, 12, 17] the lattice constant of the electrodes is xed to 2.87 A and that of M gO is taken to be $\frac{12}{2}$ larger. This, together with a 45 rotation of the Fe unit cell, allow s epitaxial m atching between Fe and M gO. In this work, the possible appearance of FeO interfacial layers as well as atom ic relaxation and disorder, are not

For the electronic structure of the junctions, we use nom -conserving pseudopotentials, double-zeta basis set for all the angular momenta and the generalized gradient approximation (GGA) [18] to the exchange and correlation potential. We have thoroughly checked that the band structure and the density of states of bulk Fe, bulk M gO and Fe/M gO multilayers, as well as the charge transfer and m agnetic m om ents in the last case, are very well reproduced as compared to FP-LAPW results obtained using the highly accurate W EN2k code [19]. W e obtain a band o set (the di erence between the Fermienergy E_F of Fe and the valence band of M gO) of 3.51 eV, in very good agreem ent with previous theoretical [20] and experim ental reports [21]. As well-known, density functional calculations using sem i-local exchange and correlation functionals underestim ate the band gap and ours are not an exception. We obtain a band gap of 5.4 eV (as compared to the experimental value of 7.8 eV [21, 22]), which agrees well with what expected from GGA [17, 20].

The ballistic transmission coe cient T (E;V) is calculated for each bias and it is given by

T (E; V) =
$$\frac{1}{V_{BZ}}^{2}$$
 dk_xdk_y T (E; V; k_x; k_y) (1)

where V_{BZ} is the area of the surface B rillouin zone orthogonal to the transport direction z. Here we assume that both spin and transverse momentum k_k are conserved, an approximation that is valid for relatively thin epitaxial junctions. The kk-resolved transmission coe cient appearing in Eq. (1) is calculated self-consistently from the non-equilibrium G reen's functions form alism in the usual way [13, 14, 16]. It is given by $T = Tr[_{L}G^{r}_{R}G^{a}]$, where for simplicity we om it the spin label . Here, Lin are the broadening matrices describing the interaction (thus the nite lifetime) of the scattering region's energy levels due to the interaction with the left and right electrodes, and G^r (G^a) is the associated retarded (advanced) G reen's function describing the one-electron dynam ics inside the scattering region. The broadening matrices are calculated from the self-energies $_{\rm L\,;R}$ as $_{\rm L:R}^{\rm Y}$). These in turn are obtained with $L_{R} = i(L_{R})$ the sem i-analytic m ethod described in reference [14].

The selfconsistent loop consists in starting from an initial density matrix of the scattering region (for example, the equilibrium -no bias-density matrix), $^{(1)}$, which gives an initial Kohn-Sham Ham iltonian H_A [⁽¹⁾] [15]. With this, the G^{r;a} can be obtained [13, 16], since L_{R} are calculated at equilibrium (V = 0) and then rigidly shifted in energy. That is, the voltagedependent selfenergies $_{L,R}$ (E;V) are therefore given eV=2;V=0). The upper (lower) sign by L;R (E in the rst argument refers to the left (right) electrode. These retarded/advanced G reen's functions are then fed into Keldysh equation for the lesser correlation $G^{<} = G^{r} < G^{a}$ [16], from which a new density matrix is obtained. In this expression, the lesser self-energy $< = \frac{1}{L} + \frac{1}{R}$ is obtained from the local equilibrium

hypothesis: $\zeta_{L;R} = if_{L;R} \downarrow_{;R}$, where f is the Ferm i-D irac distribution function corresponding to the left and right electrodes. W ith this new density matrix obtained via the K eldysh equation, the loop starts again, until convergence is achieved. We note that the selfconsistent loop must be performed at each bias voltage (because the electron population inside the scattering region, induced by the electrodes, depends on V).

In our calculations, we use a 8 8 8 k-point mesh in reciprocal space to calculate the density matrix of the scattering region and a 150 150 1 mesh to evaluate the transmission at each bias voltage. We have carefully veri ed that these meshes are su cient for converging the density matrix and the transmission.

III. RESULTS AND DISCUSSION

Starting with the single-barrier junction, in Fig. 1 we show the transm ission spectra at zero bias voltage (upper panel) and at V = 0.1 Volt (low erpanel). It is seen that, at zero bias, the P m inority channel presents a broad peak centered around $E_F + 0.1$ eV. This conductance peak is the signature of a resonance mediated by the Fe-m inority surface state located at that energy. We note that this surface state resonance is also present in a SBM TJ with n= 4 M Ls. At zero bias (or low enough bias), the Fe surface states located at both sides of the M gO barrier are approximately aligned in energy, and therefore can resonate through it. As it can be seen from the lower panel of Fig. 1, this surface state resonance is washed out by applying even a small bias voltage of 0.1 Volt. In such a situation, due to the applied bias voltage the surface states at each electrode are no longer aligned in energy. As a consequence, the resonance condition is lost and the transm ission peak disappears. Therefore, as has been already shown theoretically by Rungger et al [12] in Fe/M gO SBM TJs, transport calculations in which the transmission function is bias-independent (often taken as the zero-bias transm ission) overestim ate the contribution of surface states to the current. Here, we see a rst example showing the importance of taking into account the dependence of the transmission function on the applied bias voltage.

A nother interesting feature from Fig. 1 is that the P m a jority transm ission is alm ost independent of bias, in m arked constrast to the P m inority transm ission. This di erence is a direct consequence of the di erent transport m echanism s that govern the transm ission of each of the two P channels. The P m inority conductance is dom inated (at least for SBM TJs with thin barriers) by Fe surface states that can couple to each other directly through the M gO slab. In contrast, the P m a jority transm ission is governed by the M gO slow ly-decaying com plex band of symmetry $_1$, that can couple e ciently to the Fe B loch states of the same symmetry [17]. The com – plex bands are sm ooth functions of the energy (just as real bands are), and therefore the application of m od-

erate bias voltages has no signi cant in uence on them .



FIG.1: Transm ission spectra of a single-barrier junction with n = 2 M Ls (4 A) at zero bias (upper panel) and at V = 0.1 Volt (bwer panel).

Going over to double-barrier junctions, in Figs. 2-4 we show the transmission spectra of the DBM TJ with n=2 MLs (4 A) and m=2 MLs (2.87 A), at V=0.005Volt, 0.1 Volt and 0.15 Volt, respectively. At V = 0.005Volt (Fig. 2) the surface state resonance in the P minority channel is still observed, although the peak height is smaller than the one at zero bias shown in Fig. 1 for the single-barrier junction. That is to say, the resonant mechanism mediated by the Fe surface states can occur even in DBM TJs with very thin in-between Fe slabs, as long as the applied bias is small. As it happens in the single-barrier junction, the application of a bias voltage rapidly destroys this resonance, as it can be seen from Figs. 3 and 4 where the transmission resonance is no longer present. The origin of this feature is exactly the sam e as in SBM TJs, nam ely, the m isalignm ent in energy of the Fe surface states at each side of the barrier.

At V = 0.005 Volt (Fig. 2) and at V = 0.15 Volt (Fig. 4), the P majority transmissions are very similar to each other, being increasing linear functions of the energy. Again, this feature re ects the fact that the P majority transmission is esentially governed by the complex bands of M gO .But at V = 0.1 Volt (Fig. 3) the P m a jority transm ission is radically di erent. It is seen than it presents a sharp peak located near $E_F + 0.075$ eV. This peak is characteristic of resonant tunneling through a quantum well state inside the in-between Fe slab. This quantum well state has already been shown to be present by W ang et al [9], and we have studied its im pact on the Ι V curves of Fe/M gO (001) DBM TJs [11], reaching quantitative agreem ent with recent experim ental results [6, 7]. Therefore, from Figs. 2-4 we see that the appear-



FIG. 2: Transm ission spectra of a double-barrier junction with n=2 MLs (4 A) and m=2 MLs (2.87 A) at V=0.005 Volt.



FIG. 3: Transm ission spectra of a double-barrier junction with n = 2 M Ls (4 A) and m = 2 M Ls (2.87 A) at V = 0.1 Volt.

ance of a transm ission resonance m ediated by a quantum well state is strongly dependent on the applied bias voltage. It is very interesting to note that the resonance disappears even with very slight changes in the applied bias voltage. A change in bias of 0.05 Volt is already su cient to suppress the quantum well state resonance.

These results clearly show that, in general, it is not possible to assume that the transmission function of tunneling barriers is independent of bias, as it is usually done in non-selfconsistent calculations [8]. Both in singleand in double-barrier junctions these functions depend on bias, although the dom inant transport mechanisms are



FIG. 4: Transmission spectra of a double-barrier junction with n = 2 M Ls (4 A) and m = 2 M Ls (2.87 A) at V = 0.15 Volt.

com pletely di erent. In particular, in the double-barrier junction that we consider, the P m inority channel behaves, qualitatively, as it does in single-barrier ones, being dom inated by the resonances mediated by Fe surface states at each side of the M gO barrier. The application of a bias voltage shifts these surface states in energy, thus forbidding their direct coupling to each other. On the other hand, the P majority channel behaves di erently because in double-barrier junctions, in addition to transport m ediated by the com plex bands of M gO, another mechanism com es into play, nam ely, resonant tunneling through quantum well states. Our results are just an example of how bias-dependent is this last transport mechanism. We are currently investigating these issues in m ore detail. In particular, we are trying to understand the origin of the bias dependence of quantum well states resonances and its relation to the potential pro le inside the scattering region.

IV. CONCLUSIONS

U sing realistic models of electronic structure and selfconsistent coherent transport calculations based on nonequilibrium G reen's functions form alism, we have obtained the transmission spectra of a single-barrier and of a double-barrier Fe/M gO tunnel junction, at di erent values of the applied bias voltage. We have shown that, both in single- and double-barrier junctions, the transmission spectra depend on bias. In particular, in single-barrier junctions the application of a small bias voltage is already su cient to suppress resonances between Fe m inority surface states across the insulating barrier, a fact already discussed by Rungger et al [12]. In double-barrier junctions, the appearance of resonances m ediated by quantum well states in the majority channel is strongly dependent on the applied bias. These results bring some insight into the phenom ena of resonant tunneling through epitaxialm agnetic tunnel junctions at nite bias, and may be useful in the design and developm ent of future spin-electronic devices.

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